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- (71) Applicant: **APPLIED MATERIALS, INC.** [US/US];  
3050 Bowers Avenue, Santa Clara, California 95054 (US).
- (72) Inventors: **CHOCKALINGAM, Ashwin**; 2615 El  
Camino Real, Santa Clara, California 95051 (US). **FUNG,**

**Jason G.**; 2050 Royal Dr. Apt 43, Santa Clara, California 95050 (US). **GANAPATHIAPPAN, Sivapackia**; 161 E Portola Ave, Los Altos, California 94022 (US). **BAJAJ, Rajeev**; 43651 Skye Road, Fremont, California 94539 (US). **REDFIELD, Daniel**; 1445 Kelly Park Circle, Morgan Hill, California 95037 (US).

(74) Agent: **PATTERSON, B. Todd** et al.; 24 Greenway Plaza, Suite 1600, Houston, Texas 77046 (US).

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(54) Title: POLISHING PADS FORMED USING AN ADDITIVE MANUFACTURING PROCESS AND METHODS RELATED THERETO

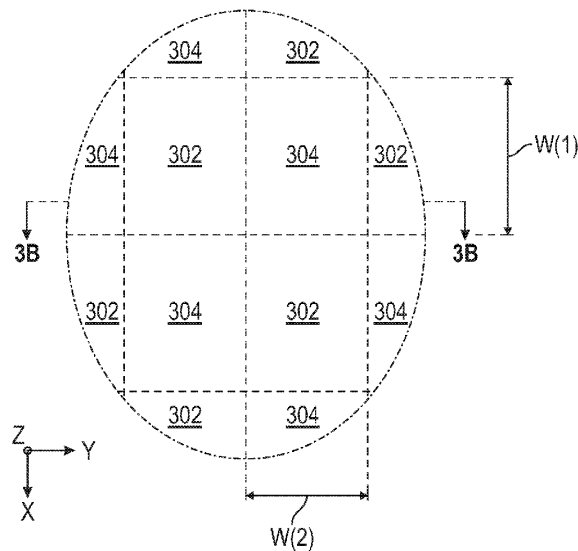


FIG. 3A

(57) Abstract: Embodiments of the present disclosure generally relate to polishing pads, and methods for manufacturing polishing pads, which may be used in a chemical mechanical polishing (CMP) process in the manufacture of semiconductor devices. The polishing pads described herein feature a continuous polymer phase of polishing pad material comprising one or more first material domains and a plurality of second material domains. The one or more first material domains are formed of a polymerized reaction product of a first pre-polymer composition, the plurality of second material domains are formed of a polymerized reaction product of a second pre-polymer composition, the second pre-polymer composition is different from the first pre-polymer composition, and interfacial regions between the one or more first material domains and the plurality of second material are formed of a co-polymerized reaction product of the first pre-polymer composition and the second pre-polymer composition.

[Continued on next page]

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